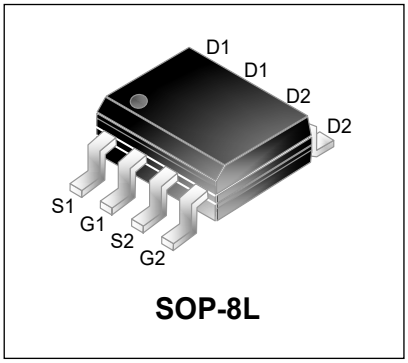
WM03DH60A

N+P Dual Channel Enhancement MOSFET

Features



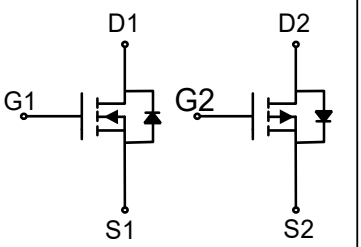
SOP-8L

- Way-on Small Signal MOSFETs
- N - Channel：
  V_{DS}= 30V, I_D = 5.8A
  $R_{DS(on)}$ < 36 mΩ @ V_{GS} = 10V
  $R_{DS(on)}$ < 45 mΩ @ V_{GS} = 4.5V
- P - Channel：
  V_{DS}= -30V, I_D = -6A
  $R_{DS(on)}$ < 24 mΩ @ V_{GS} = -10V
  $R_{DS(on)}$ < 35 mΩ @ V_{GS} = -4.5V
- Trench LV MOSFET Technology

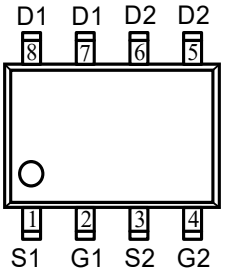
Mechanical Characteristics

- SOP-8L Package
- Marking : Making Code
- RoHS Compliant

Schematic & PIN Configuration



Device symbol



SOP-8L(Top View)

Absolute Maximum Ratings (T_A=25°C unless otherwise noted)

Parameter		Symbol	Value		Unit
Drain-Source Voltage		V_{DS}	30	-30	V
Gate-Source Voltage		V_{GS}	±20	±20	V
Continuous Drain Current	T_A=25°C	I_D	5.8	-6	A
Pulsed Drain Current[1]		I_{DM}	23.2	-24	A
Power Dissipation	T_A=25°C	P_D	1.2		W
Operating Junction and Storage Temperature Range		T_J, T_{STG}	-55 to 150		°C

Thermal Characteristics

Parameter	Symbol	Value	Unit
Thermal Resistance from Junction to Ambient[2]	$R_{\theta JA}$	104	°C/W

Electrical Characteristics N-Channel (T_J=25°C unless otherwise noted)

Parameter	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Static Characteristics						
Drain-Source Breakdown Voltage	BV_{DSS}	V_{GS} = 0 V, I_D = 250μA	30	-	-	V
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS} =30V, V_{GS} = 0 V	-	-	1	μA
Gate-Body Leakage Current	I_{GSS}	V_{DS} = 0 V, V_{GS} = ±20V	-	-	±100	nA
Gate Threshold Voltage	$V_{GS(th)}$	V_{GS}= V_{DS}, I_D = 250μA	1	1.5	2.5	V
Drain-Source on-State Resistance[3]	$R_{DS(on)}$	V_{GS} = 10V, I_D = 5.8A	-	25	36	mΩ
		V_{GS} = 4.5V, I_D = 4.8A	-	35	45	
Dynamic Characteristics[4]						
Input Capacitance	C_{iss}	V_{GS} = 0V, V_{DS} = 15V, f = 1MHz	-	500	-	pF
Output Capacitance	C_{oss}		-	72	-	
Reverse Transfer Capacitance	C_{rss}		-	58	-	
Switching Characteristics[4]						
Total Gate Charge	Q_g	V_{DS}= 15V, V_{GS}= 4.5V, I_D = 5.8A	-	7.5	-	nC
Gate−Source Charge	Q_{gs}		-	1.6	-	
Gate−Drain Charge	Q_{gd}		-	2.1	-	
Turn-on Delay Time	$t_{d(on)}$	V_{DD}= 15V, V_{GS}= 10V, R_G=3Ω, I_D=5.8A	-	6.4	-	ns
Turn-on Rise Time	t_r		-	3.1	-	
Turn-off Delay Time	$t_{d(off)}$		-	15.0	-	
Turn- off Fall Time	t_f		-	2.6	-	
Source-Drain Diode Characteristics						
Body Diode Voltage[3]	V_{SD}	I_S=1A, V_{GS} = 0V	-	-	1.2	V
Continuous Source Current	I_S		-	-	5.8	A

Notes:

1. Repetitive rating, pulse width limited by junction temperature $T_{J(MAX)}$=150°C.

2. The data tested by surface mounted on a 1 inch2 FR-4 board with 2OZ copper, The value in any given application depends on the user's specific board design.

3. Pulse Test: Pulse width≤300μs, duty cycle≤2%.

4. This value is guaranteed by design hence it is not included in the production test.

Electrical Characteristics P-Channel (T_J=25°C unless otherwise noted)

Parameter	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Static Characteristics						
Drain-Source Breakdown Voltage	BV_{DSS}	V_{GS} = 0V, I_D = -250μA	-30	-	-	V
Gate-body Leakage Current	I_{GSS}	V_{DS} = 0V, V_{GS} = ±20V	-	-	±100	nA
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS} = -30V, V_{GS} = 0V	-	-	-1	μA
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS} = V_{GS}, I_D = -250μA	-1	-1.5	-3	V
Drain-Source On-state Resistance[3]	$R_{DS(on)}$	V_{GS} = -10V, I_D = -6A	-	17	24	mΩ
		V_{GS} = -4.5V, I_D = -5A	-	23	35	
Dynamic Characteristics[4]						
Input Capacitance	C_{iss}	V_{GS} = 0V, V_{DS} = -15V, f = 1MHz	-	1550	-	pF
Output Capacitance	C_{oss}		-	200	-	
Reverse Transfer Capacitance	C_{rss}		-	175	-	
Switching Characteristics[4]						
Total Ggate Charge	Q_g	V_{GS}= -10V, I_D = -6A, V_{DS} = -15V	-	30	-	nC
Gate-Source Charge	Q_{gs}		-	5.5	-	
Gate-Drain Charge	Q_{gd}		-	8	-	
Turn-On Delay Time	$t_{d(on)}$	V_{GS} = -10V,V_{DD}= -15V, R_G = 3Ω, I_D = -6A	-	10	-	ns
Turn-On Rise Time	t_r		-	15	-	
Turn-Off Delay Time	$t_{d(off)}$		-	110	-	
Turn- Off Fall Time	t_f		-	70	-	
Source-Drain Diode characteristics						
Body Diode Voltage[3]	V_{DS}	I_S= -1A, V_{GS} = 0V	-	-	-1.2	V
Continuous Source Current	I_S		-	-	-6	A

Notes:

1. Repetitive rating, pulse width limited by junction temperature $T_{J(MAX)}$=150°C.
2. The data tested by surface mounted on a 1 inch2 FR-4 board with 2OZ copper, The value in any given application depends on the user's specific board design.
3. Pulse Test: Pulse width≤300μs, duty cycle≤2%.
4. This value is guaranteed by design hence it is not included in the production test.

Typical Characteristics：N-Channel

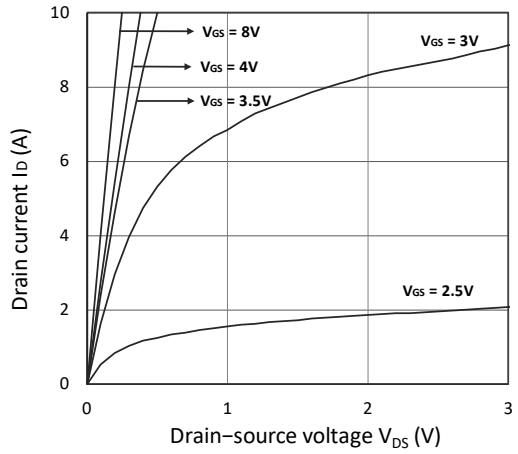


Figure 1. Output Characteristics

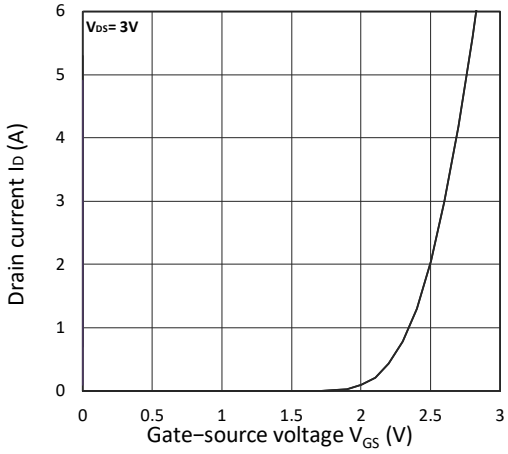


Figure 2. Transfer Characteristics

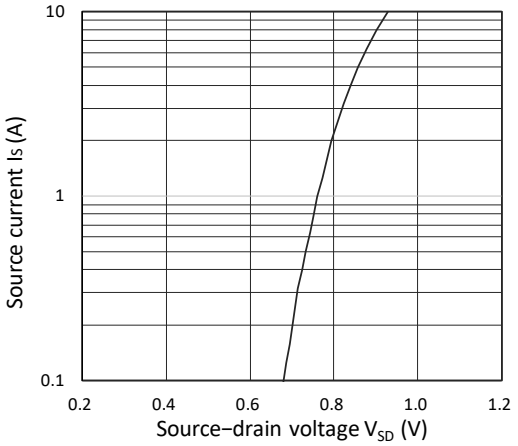


Figure 3. Forward Characteristics of Reverse

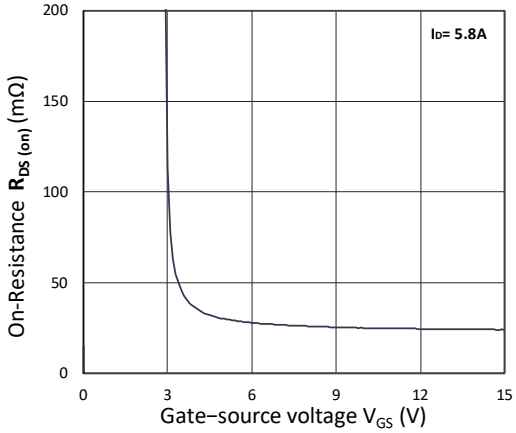


Figure 4. $R_{DS(ON)}$ vs. V_{GS}

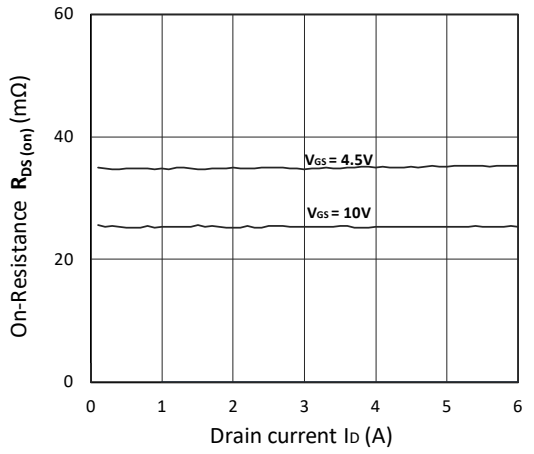


Figure 5. $R_{DS(ON)}$ vs. I_D

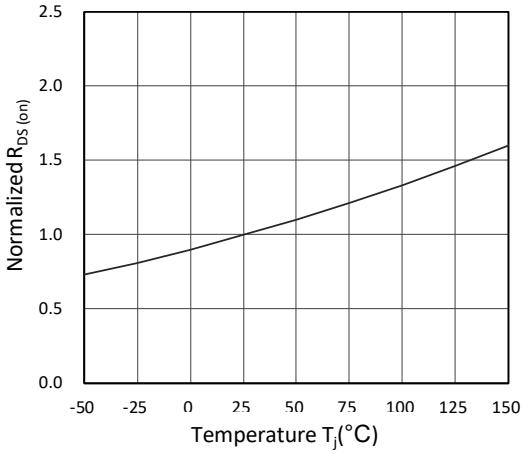


Figure 6. Normalized $R_{DS(on)}$ vs. Temperature

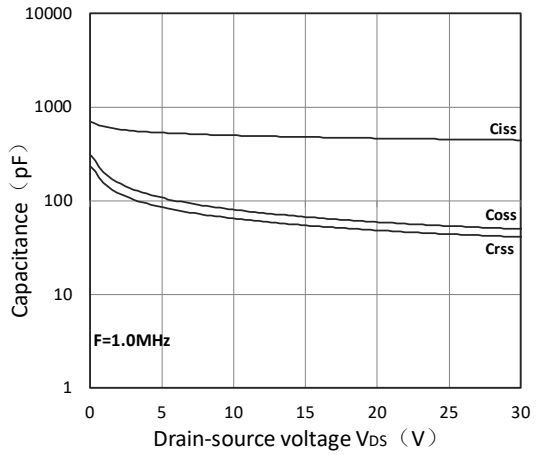


Figure 7. Capacitance Characteristics

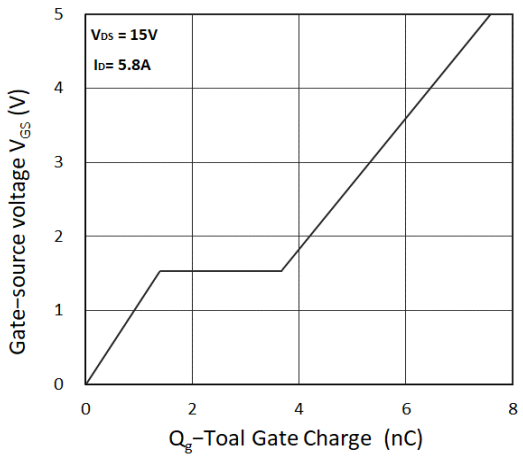


Figure 8. Gate Charge Characteristics

Typical Characteristics：P-Channel

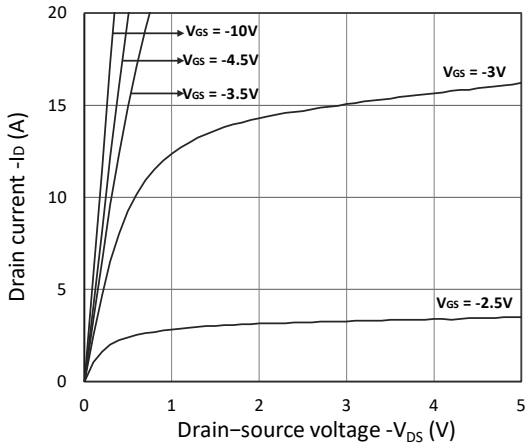


Figure 1. Output Characteristics

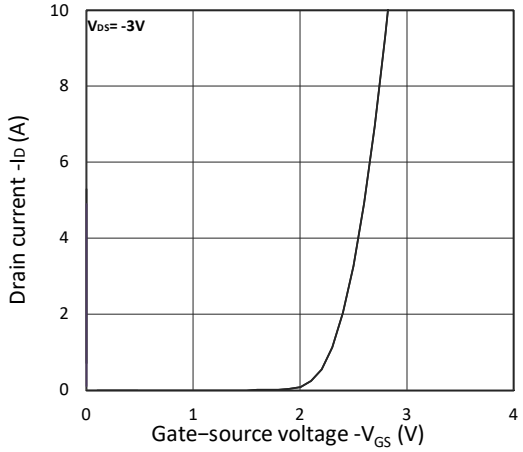


Figure 2. Transfer Characteristics

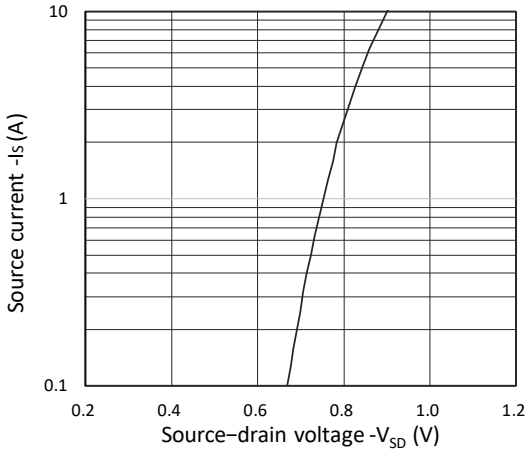


Figure 3. Forward Characteristics of Reverse

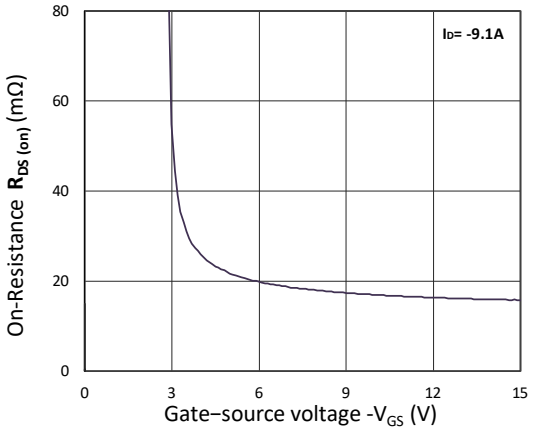


Figure 4. $R_{DS(ON)}$ vs. V_{GS}

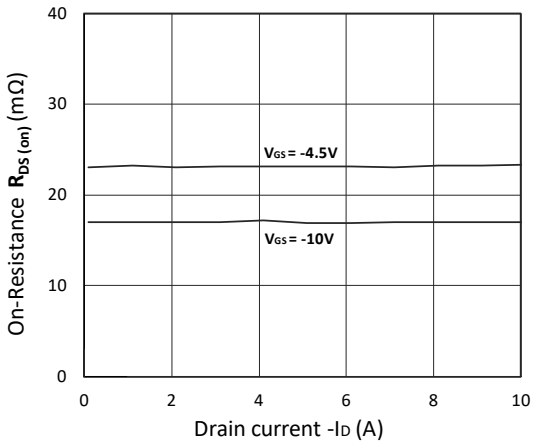


Figure 5. $R_{DS(ON)}$ vs. I_D

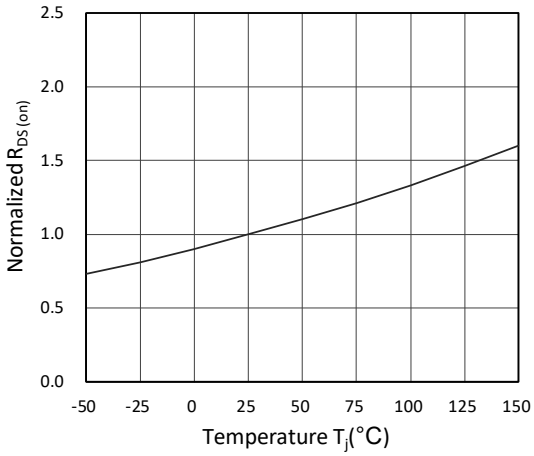
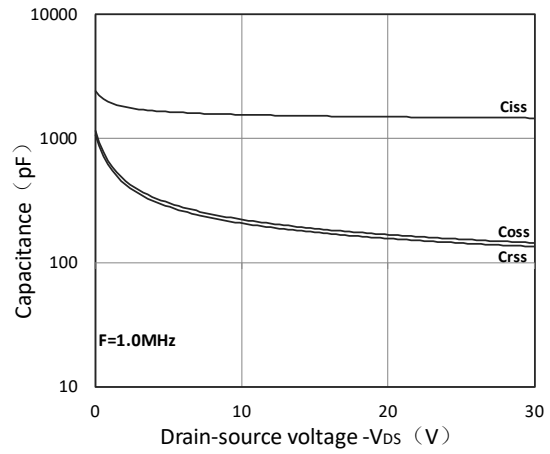


Figure 6. Normalized $R_{DS(on)}$ vs. Temperature



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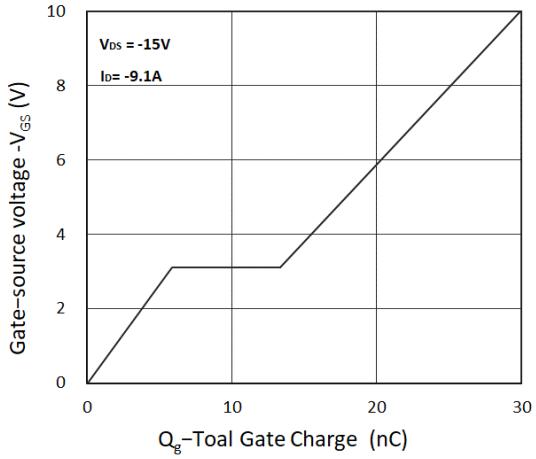
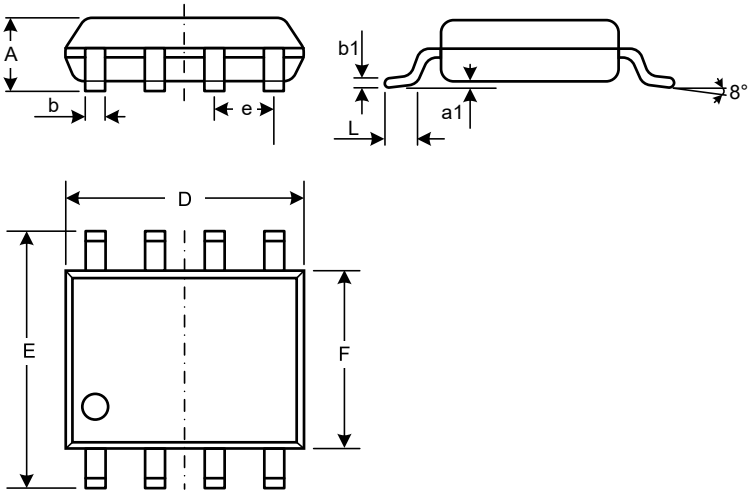
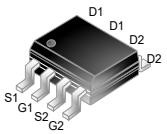


Figure 8. Gate Charge Characteristics

Outline Drawing – SOP-8L

PACKAGE OUTLINE

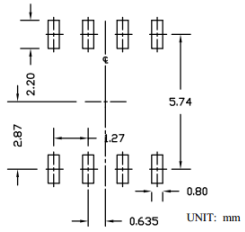




SOP-8L

DIMENSIONS

SYMBOL	MILLIMETER		INCHES	
	MIN	MAX	MIN	MAX
A	1.35	1.75	0.053	0.069
a1	0.05	0.25	0.002	0.010
b	0.31	0.51	0.012	0.020
b1	0.16	0.25	0.006	0.010
D	4.70	5.15	0.185	0.203
E	5.75	6.25	0.226	0.246
e	1.07	1.47	0.042	0.058
F	3.70	4.10	0.146	0.161
L	0.40	1.27	0.016	0.050



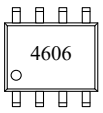
Notes

1. Dimensioning and tolerances per ANSI Y14.5M, 1985.

2. Controlling Dimension: Inches

3. Dimensions are exclusive of mold flash and metal burrs.

Marking Codes

Part Number	WM03DH60A
Marking Code	

Package Information

Qty：4k/Reel

CONTACT INFORMATION

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WAYON website: **http://www.way-on.com**
For additional information, please contact your local Sales Representative.

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Specifications are subject to change without notice.
The device characteristics and parameters in this data sheet can and do vary in different applications and actual device performance may vary over time.
Users should verify actual device performance in their specific applications.